

HAT2167N

Silicon N Channel Power MOS FET Power Switching

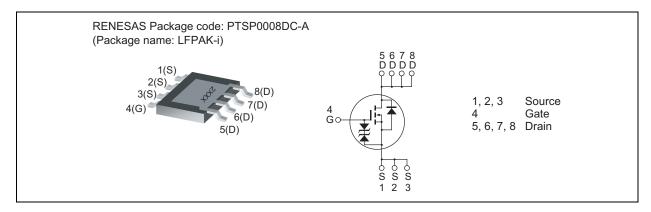
REJ03G1681-0200 Rev.2.00 May 27, 2008

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 4.5~\text{m}\Omega$ typ. (at $V_{GS} = 10~\text{V})$

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I _D	40	Α
Drain peak current	I _{D(pulse)} Note1	160	A
Body-drain diode reverse drain current	I _{DR}	40	A
Avalanche current	I _{AP} Note 2	20	A
Avalanche energy	E _{AR} Note 2	40	mJ
Channel dissipation	Pch Note3	20	W
Channel to case thermal resistance	θch-C	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tch = 25°C, Rg \geq 50 Ω

3. $Tc = 25^{\circ}C$

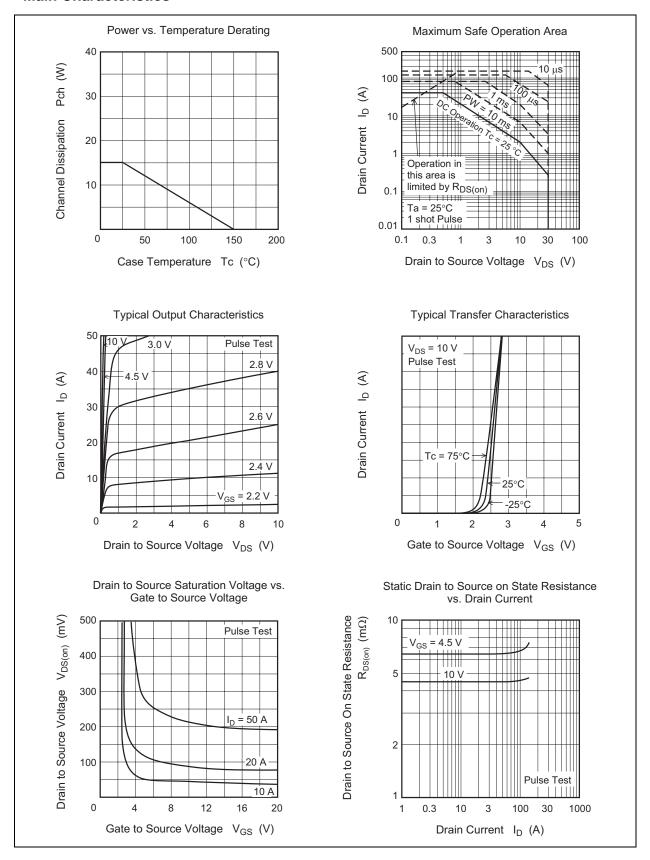
Electrical Characteristics

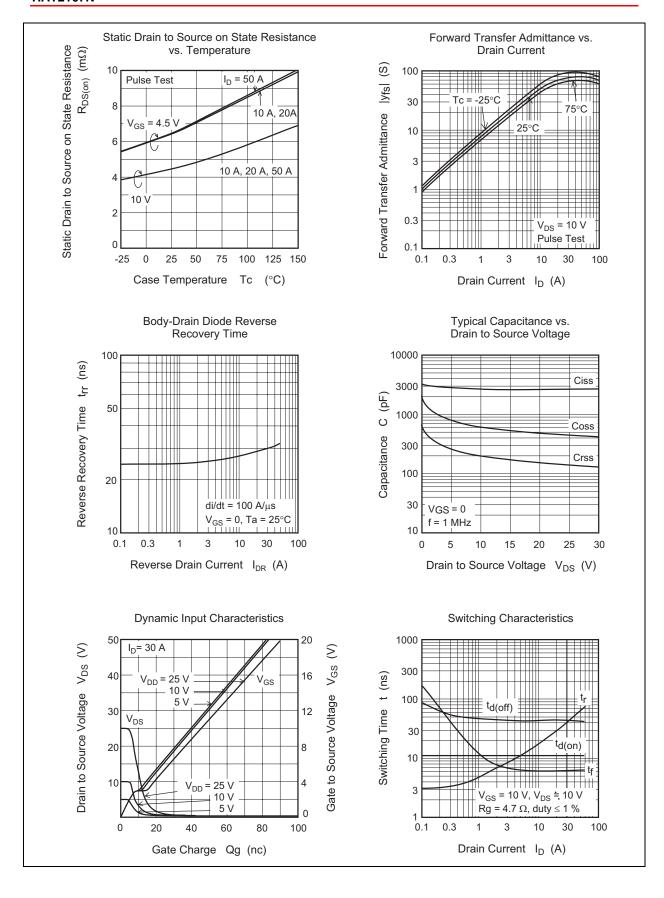
 $(Ta = 25^{\circ}C)$

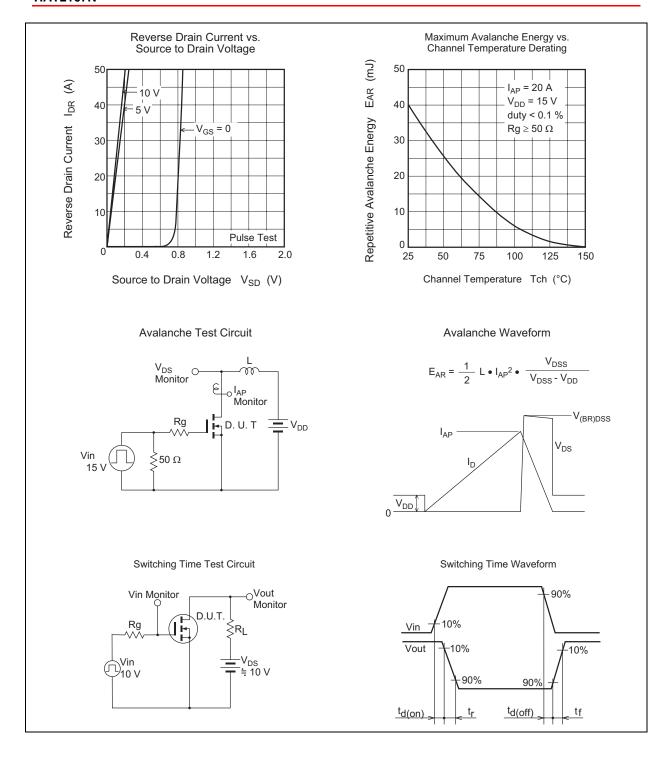
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	4.5	5.8	mΩ	$I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}	_	6.4	9.6	mΩ	$I_D = 20 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	42	70	_	S	$I_D = 20 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2700	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	620	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	200	_	pF	f = 1 MHz
Gate resistance	Rg	_	0.5	_	Ω	
Total gate charge	Qg	_	17	_	nc	$V_{DD} = 10 \text{ V}$
Gate to source charge	Qgs	_	8	_	nc	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Qgd	_	3.7	_	nc	$I_D = 40 \text{ A}$
Turn-on delay time	t _{d(on)}	_	11	_	ns	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$
Rise time	t _r	_	30	_	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	t _{d(off)}	_	45	_	ns	$R_L = 0.5 \Omega$
Fall time	t _f	_	6	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	_	0.85	1.10	V	$I_F = 40 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body–drain diode reverse recovery time	t _{rr}	_	30	_	ns	$I_F = 40 \text{ A}, V_{GS} = 0$ $di_F / dt = 100 \text{ A} / \mu \text{s}$

Notes: 4. Pulse test

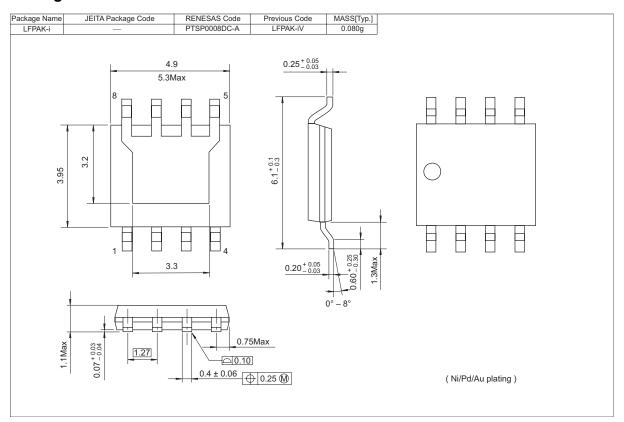
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2167N-EL-E	2500 pcs	Taping

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